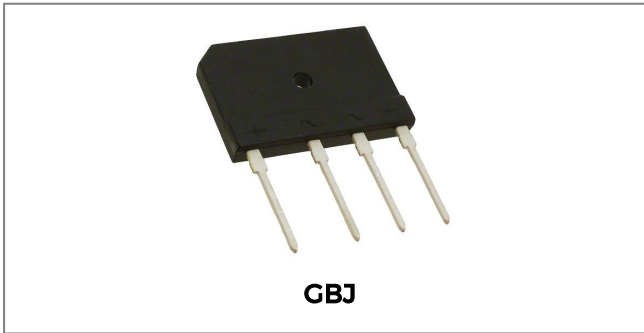


## GBJ10005-GBJ1010

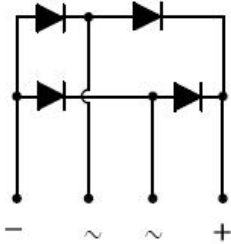
### Single-Phase 10.0A Glass Passivated Bridge Rectifier



#### Features

- Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### Circuit Diagram



#### Mechanical Data

- Case: GBJ, Molded plastic
- Terminals: Plated leads solderable per MIL-STD-202, Method 208
- Polarity: as marked on case
- Mounting Position: Any
- Lead Free: For RoHS / Lead Free Version
- Weight: 6.8 grams(approx)

#### Maximum Ratings @T<sub>A</sub>=25°C unless otherwise specified

Type Number	Symbol	GBJ 10005	GBJ 1001	GBJ 1002	GBJ 1004	GBJ 1006	GBJ 1008	GBJ 1010	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_{DC}$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Average rectified output current (with heatsink)@T <sub>C</sub> = 100°C (without heatsink)@T <sub>A</sub> = 25°C	$I_{F(AV)}$	10 3.5							A
Peak Forward Surge Current, 8.3ms single half-sine-wave superimposed on rated load (JEDEC method) @T <sub>J</sub> = 25°C @T <sub>J</sub> = 125°C	$I_{FSM}$	240 192							A
I <sup>2</sup> t Rating for Fusing (t < 8.3ms)	I <sup>2</sup> t	239							A <sup>2</sup> s

**Electrical Characteristics@T<sub>A</sub>=25°C unless otherwise specified**

Type Number	Symbol	GBJ 10005	GBJ 1001	GBJ 1002	GBJ 1004	GBJ 1006	GBJ 1008	GBJ 1010	Units
Forward Voltage (per element) @I <sub>F</sub> =5A @I <sub>F</sub> =10A	V <sub>F</sub>	1.0 1.1							V
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 125°C	I <sub>RM</sub>	5.0 200							μA
Dielectric Strength	V <sub>ids</sub>	2500							V
The proposed installation torque Max torque	T <sub>or</sub>	Typ. 5.0 Max 8.0							Kgf.cm
Typical Junction Capacitance(per leg) (Note 1)	C <sub>J</sub>	70							pF

\* Pulse width < 300 μs, duty cycle < 2%

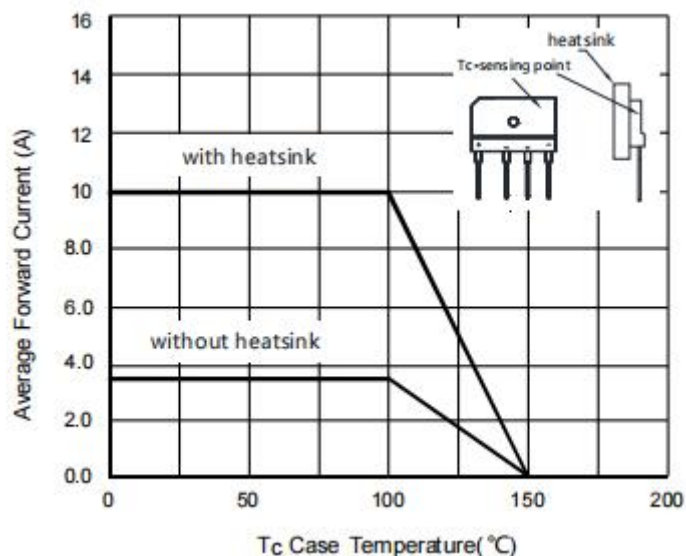
**Thermal-Mechanical Specifications:**

Type Number	Symbol	GBJ 10005	GBJ 1001	GBJ 1002	GBJ 1004	GBJ 1006	GBJ 1008	GBJ 1010	Units
Typical Thermal Resistance Junction	R <sub>θJA</sub> R <sub>θJL</sub> R <sub>θJC</sub>	22 3 5							°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150							°C

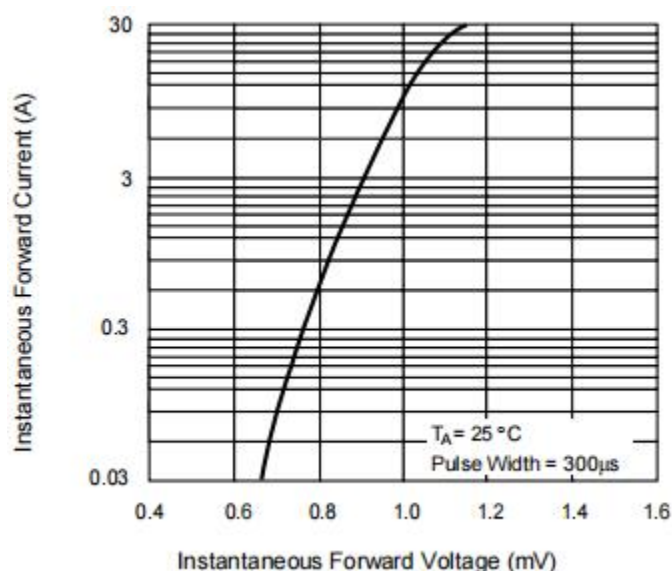
Note: 1. Measured at 1.0 MHz and applied reverse voltage of 5.0V D.C.

**Ratings and Characteristics Curves**

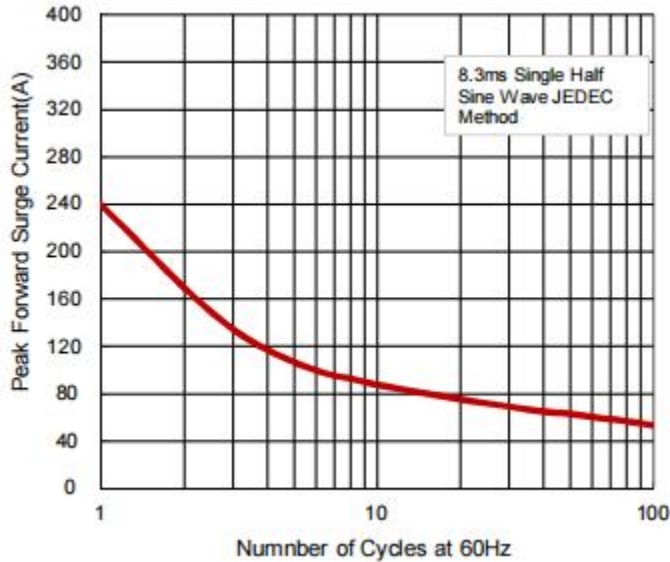
**Fig. 1 Output Current Derating Curve**



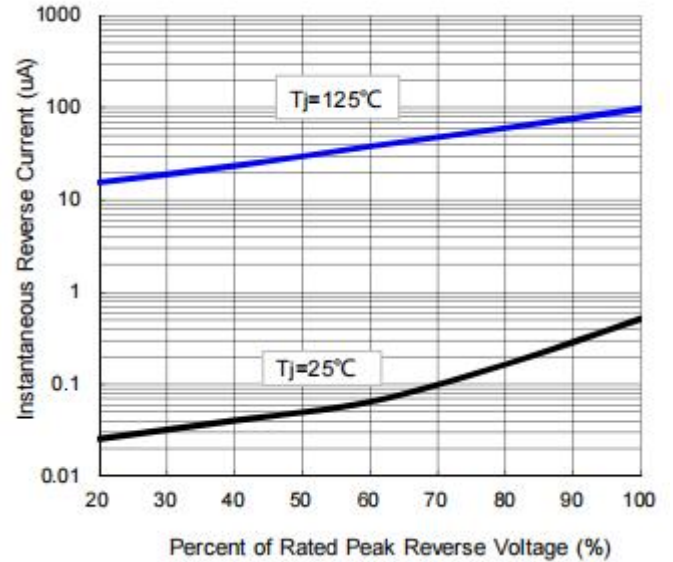
**Fig. 2 Typical Forward Characteristics**



**Fig. 3 Forward Surge Current Capability**



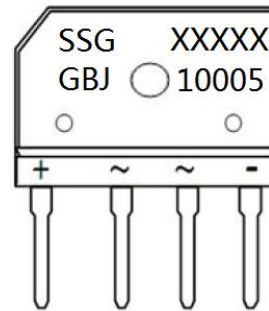
**Fig. 4 Typical Reverse Characteristics**



## Ordering Information

Device	Package	Plating	Shipping
GBJ10005 THRU GBJ1010	GBJ(Pb-Free)	Pure Sn	15pcs / tube

## Marking Diagram

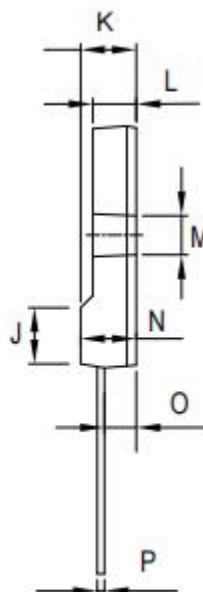
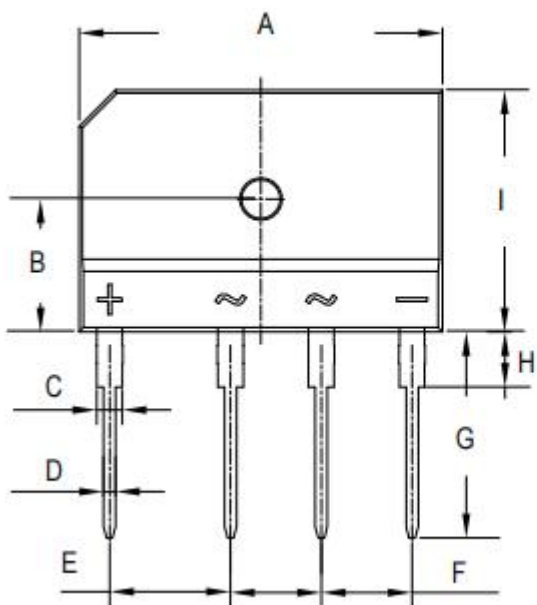


Where XXXXX is YYWWL

SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number  
GBJ10005 = Type Number

**Cautions:** Molding resin  
Epoxy resin UL94V-0

**Mechanical Dimensions GBJ (Inches/Millimeters)**



Dimensions	Millimeters		Inches	
	Min	Max	Min	Max
A	29.7	30.3	1.169	1.193
B	10.8	11.2	0.425	0.441
C	1.9	2.3	0.075	0.091
D	0.9	1.1	0.035	0.043
E	9.8	10.2	0.386	0.402
F	7.3	7.7	0.287	0.303
G	17.0	18.0	0.699	0.709
H	3.8	4.2	0.150	0.165
I	19.7	20.3	0.776	0.799
J	4.8	5.2	0.189	0.205
K	4.4	4.8	0.173	0.189
L	3.4	3.8	0.134	0.150
M	3.1	3.4	0.122	0.134
N	4.4	4.8	0.173	0.189
O	2.4	2.8	0.094	0.110
P	0.5	0.7	0.020	0.028

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